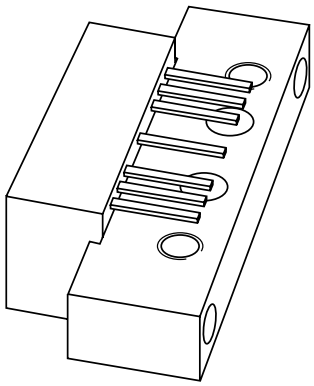
DATA SHEET



BGY787

750 MHz, 21.5 dB gain push-pull amplifier

Product specification
Supersedes data of 1999 Mar 30

2001 Oct 31

Philips
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750 MHz, 21.5 dB gain push-pull amplifier BGY787

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

CATV systems operating over a 40 to 750 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2	common
3	common
5	$+V_B$
7	common
8	common
9	output

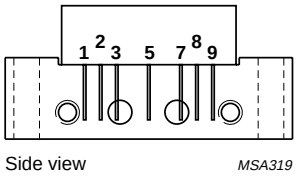


Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	f = 50 MHz	21	22	dB
		f = 750 MHz	21.5	–	dB
I_{tot}	total current consumption (DC)	V_B = 24 V	–	240	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_i	RF input voltage	–	60	dBmV
T_{stg}	storage temperature	–40	+100	°C
T_{mb}	mounting base operating temperature	–20	+100	°C

CHARACTERISTICS

Table 1 Bandwidth 40 to 750 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	21	21.5	22	dB
		f = 750 MHz	21.5	22.5	–	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0	1	1.5	dB
FL	flatness of frequency response	f = 40 to 750 MHz	–	±0.2	±0.5	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	33	–	dB
		f = 80 to 160 MHz	18.5	30	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 640 MHz	15.5	22.5	–	dB
		f = 640 to 750 MHz	14	20.5	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	27.5	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 640 MHz	15.5	22	–	dB
		f = 640 to 750 MHz	14	20	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	110 channels flat; V_o = 44 dBmV; measured at 745.25 MHz	–	–54.5	–53	dB
X_{mod}	cross modulation	110 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–54	–52	dB
CSO	composite second order distortion	110 channels flat; V_o = 44 dBmV; measured at 746.5 MHz	–	–57.5	–53	dB
d_2	second order distortion	note 1	–	–75	–63	dB
V_o	output voltage	d_{im} = –60 dB; note 2	61	63	–	dBmV
F	noise figure	f = 50 MHz	–	4	5	dB
		f = 450 MHz	–	–	5.5	dB
		f = 550 MHz	–	–	5.5	dB
		f = 600 MHz	–	–	6	dB
		f = 750 MHz	–	5	6.5	dB
I_{tot}	total current consumption (DC)	note 3	–	220	240	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 691.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 746.5 MHz.
2. Measure according to DIN45004B;
   f_p = 740.25 MHz; $V_p = V_o$;
   f_q = 747.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 749.25 MHz; $V_r = V_o$–6 dB;
   measured at $f_p + f_q - f_r$ = 738.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 2 Bandwidth 40 to 600 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	21	21.5	22	dB
		f = 600 MHz	21.5	–	–	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0	–	1.5	dB
FL	flatness of frequency response	f = 40 to 600 MHz	–	–	±0.3	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	33	–	dB
		f = 80 to 160 MHz	18.5	30	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 600 MHz	16	22.5	–	dB
s_{22}	output return losses	f = 40 to 80 MHz;	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	27.5	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 600 MHz	16	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	85 channels flat; V_o = 44 dBmV; measured at 595.25 MHz	–	–59.5	–58	dB
X_{mod}	cross modulation	85 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–55.5	–53	dB
CSO	composite second order distortion	85 channels flat; V_o = 44 dBmV; measured at 596.5 MHz	–	–64	–56	dB
d_2	second order distortion	note 1	–	–	–68	dB
V_o	output voltage	d_{im} = –60 dB; note 2	62.5	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	220	240	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 541.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 596.5 MHz.
2. Measure according to DIN45004B;
   f_p = 590.25 MHz; $V_p = V_o$;
   f_q = 597.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 599.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 588.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 3 Bandwidth 40 to 550 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	21	21.5	22	dB
		f = 550 MHz	21.5	–	–	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0	–	1.5	dB
FL	flatness of frequency response	f = 40 to 550 MHz	–	–	±0.3	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	33	–	dB
		f = 80 to 160 MHz	18.5	30	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 550 MHz	16	22.5	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	27.5	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 550 MHz	16	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	77 channels flat; V_o = 44 dBmV; measured at 547.25 MHz	–	–61	–60	dB
X_{mod}	cross modulation	77 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–56.5	–55	dB
CSO	composite second order distortion	77 channels flat; V_o = 44 dBmV; measured at 548.5 MHz	–	–65.5	–58	dB
d_2	second order distortion	note 1	–	–	–70	dB
V_o	output voltage	d_{im} = –60 dB; note 2	63	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	220	240	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 493.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 548.5 MHz.
2. Measure according to DIN45004B;
   f_p = 540.25 MHz; $V_p = V_o$;
   f_q = 547.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 549.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 538.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 4 Bandwidth 40 to 450 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

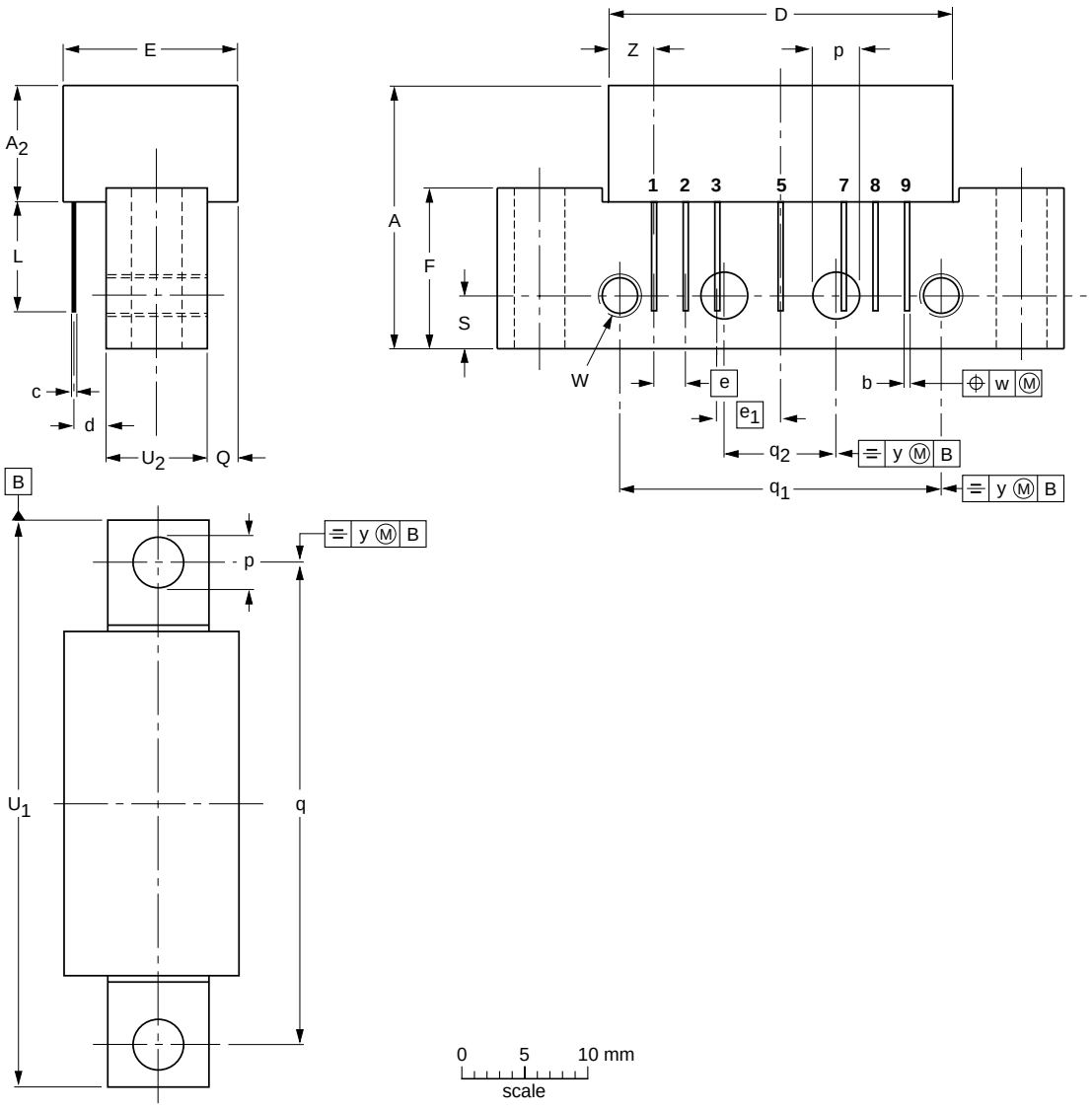
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	21	21.5	22	dB
		f = 450 MHz	21.5	–	–	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0	–	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	–	–	±0.3	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	33	–	dB
		f = 80 to 160 MHz	18.5	30	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 450 MHz	16	22.5	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	28.5	–	dB
		f = 80 to 160 MHz	18.5	27.5	–	dB
		f = 160 to 320 MHz	17	25	–	dB
		f = 320 to 450 MHz	16	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	60 channels flat; V_o = 46 dBmV; measured at 445.25 MHz	–	–	–59	dB
X_{mod}	cross modulation	60 channels flat; V_o = 46 dBmV; measured at 55.25 MHz	–	–	–54	dB
CSO	composite second order distortion	60 channels flat; V_o = 46 dBmV; measured at 446.5 MHz	–	–	–60	dB
d_2	second order distortion	note 1	–	–	–73	dB
V_o	output voltage	d_{im} = –60 dB; note 2	64	–	–	dBmV
F	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	220	240	mA

Notes

1. f_p = 55.25 MHz; V_p = 46 dBmV;
   f_q = 391.25 MHz; V_q = 46 dBmV;
   measured at $f_p + f_q$ = 446.5 MHz.
2. Measure according to DIN45004B;
   f_p = 440.25 MHz; $V_p = V_o$;
   f_q = 447.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 449.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 438.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads **SOT115J**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_2 max.	b	c	D max.	d max.	E max.	e	e_1	F	L min.	p	Q max.	q	q_1	q_2	S	U_1 max.	U_2	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

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